

ZXMP6A16K 60V DPAK P-channel enhancement mode MOSFET

Summary

V _{(BR)DSS}	R _{DS(on)} (Ω)	I _D (A)
-60	0.085 @ V _{GS} = -10V	8.2
	0.125 @ V _{GS} = -4.5V	6.75



Description

This new generation trench MOSFET from Zetex features a unique structure combining the benefits of low on-resistance and fast switching, making it ideal for high efficiency power management applications.

Features

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- DPAK package

Applications

- DC-DC converters
- Power management functions
- Disconnect switches
- Motor control

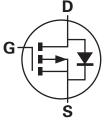
Ordering information

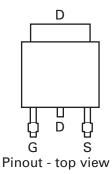
Device	Reel size	Tape width	Quantity	
	(inches)	(mm)	per reel	
ZXMP6A16KTC	13	16	2500	

Device marking

ZXMP 6A16

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Absolute maximum ratings

Parameter	Symbol	Limit	Unit
Drain-source voltage	V _{DSS}	-60	V
Gate-source voltage	V _{GS}	± 20	V
Continuous drain current @V _{GS} = 10V; T _{amb} =25°C ^(b)	۱ _D	8.2	А
@ V _{GS} = 10V; T _{amb} =70°C ^(b)		6.5	
@ V _{GS} = 10V; T _{amb} =25°C ^(a)		5.4	
Pulsed drain current ^(c)	I _{DM}	27.2	А
Continuous source current (body diode) ^(b)	۱ _S	10	А
Pulsed source current (body diode) ^(c)	I _{SM}	27.2	А
Power dissipation at $T_{amb} = 25^{\circ}C^{(a)}$	P _D	4.24	W
Linear derating factor		33.9	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(b)}$	P _D	9.76	W
Linear derating factor		78	mW/°C
Power dissipation at $T_{amb} = 25^{\circ}C^{(d)}$	PD	2.11	W
Linear derating factor		16.8	mW/°C
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

Thermal resistance

Parameter	Symbol	Limit	Unit
Junction to ambient ^(a)	$R_{\Theta JA}$	29.45	°C/W
Junction to ambient ^(b)	$R_{\Theta JA}$	12.8	°C/W
Junction to ambient ^(d)	R_{\ThetaJA}	59.1	°C/W

NOTES:

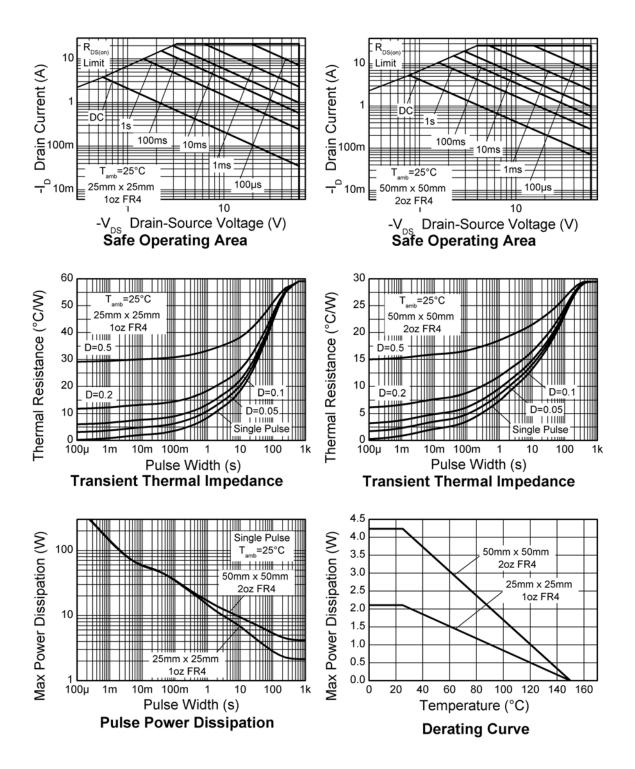
(a) For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions.

(b)For a device surface mounted on FR4 PCB measured at t ${\leq}10$ sec.

(c) Repetitive rating 50mm x 50mm x 1.6mm FR4 PCB, D=0.02 pulse width=300µs - pulse width limited by maximum junction temperature.

(d) For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

Thermal characteristics



Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions	
Static						1	
Drain-source breakdown voltage	V _{(BR)DSS}	-60			V	I _D = -250μA, V _{GS} =0V	
Zero gate voltage drain current	I _{DSS}			-1.0	μA	V _{DS} = -60V, V _{GS} =0V	
Gate-body leakage	I _{GSS}			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Gate-source threshold voltage	V _{GS(th)}	-1.0			V	I_{D} = -250 μ A, V_{DS} =VGS	
Static drain-source on-state resistance ^(*)	R _{DS(on)}			0.085	Ω	V _{GS} = -10V, I _D = -2.9A	
				0.125	Ω	V_{GS} = -4.5V, I_{D} = -2.4A	
Forward transconductance ^{(*) (‡)}	9 _{fs}		7.2		S	V _{DS} = -15V, I _D = -2.9A	
Dynamic ^(‡)	•	•		•			
Input capacitance	C _{iss}		1021		pF	V _{DS} = -30V, V _{GS} =0V	
Output capacitance	C _{oss}		83		pF	f=1MHz	
Reverse transfer capacitance	C _{rss}		56		pF		
Switching ^{(†) (‡)}						1	
Turn-on-delay time	t _{d(on)}		3.5		ns	V _{DD} = -30V, I _D = -1A	
Rise time	t _r		4.1		ns	R _G ≅6.0Ω, V _{GS} = -10V	
Turn-off delay time	t _{d(off)}		35		ns		
Fall time	t _f		10		ns		
Gate charge	0 _g		12.1		nC	V _{DS} = -30V, V _{GS} = -5V I _D = -2.9A	
Total gate charge	Qg		24.2		nC	V _{DS} = -30V, V _{GS} = -10V	
Gate-source charge	Q _{gs}		2.5		nC	I _D = -2.9A	
Gate drain charge	Q _{gd}		3.7		nC		
Source-drain diode							
Diode forward voltage ^(*)	V _{SD}		-0.85	-0.95	V	T _j =25°C, I _S = -3.4A, V _{GS} =0V	
Reverse recovery time ^(‡)	t _{rr}		29.2		ns	T _j =25°C, I _S = -2A,	
Reverse recovery charge ^(‡)	Q _{rr}		39.6		nC	di/dt=100A/µs	

Electrical characteristics (at $T_{amb} = 25^{\circ}C$ unless otherwise stated)

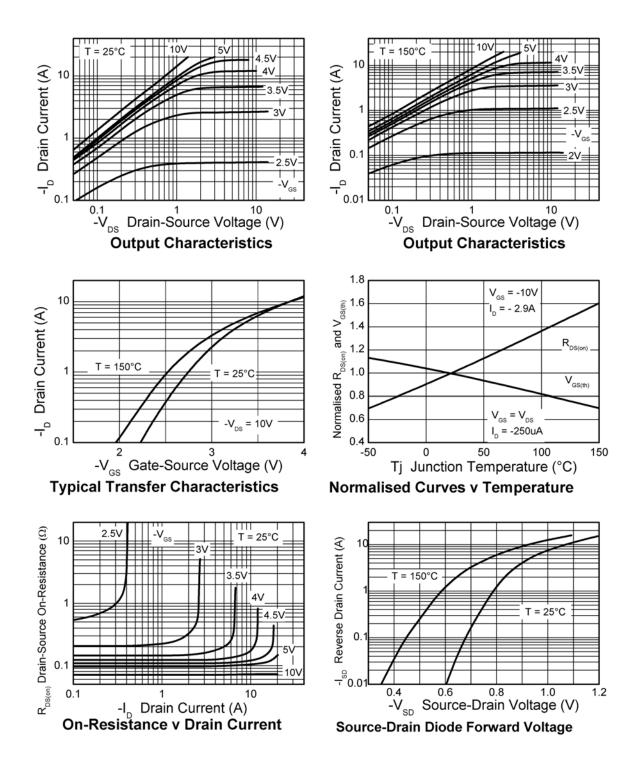
NOTES:

(*) Measured under pulsed conditions. Pulse width = 300 $\mu s.$ Duty cycle ${\leq}2\%.$

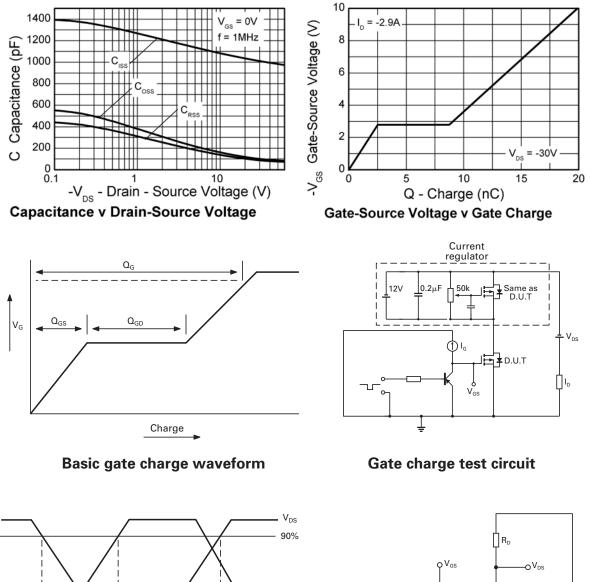
(†) Switching characteristics are independent of operating junction temperature.

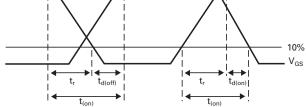
(‡) For design aid only, not subject to production testing.

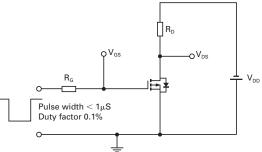
Typical characteristics



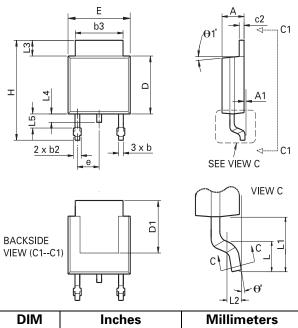
Typical characteristics







Package outline - DPAK



DIM	Inc	hes	Millin	neters	DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
Α	0.086	0.094	2.18	2.39	е	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	Н	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020) BSC	0.508	BSC
С	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	θ1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	θ°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

Note: Controlling dimensions are in inches. Approximate dimensions are provided in millimeters

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Europe	Americas	Asia Pacific	Corporate Headquarters
Zetex GmbH Kustermann-park Balanstraße 59 D-81541 München Germany	Zetex Inc 700 Veterans Memorial Highway Hauppauge, NY 11788 USA	Zetex (Asia Ltd) 3701-04 Metroplaza Tower 1 Hing Fong Road, Kwai Fong Hong Kong	Zetex Semiconductors plc Zetex Technology Park, Chadderton Oldham, OL9 9LL United Kingdom
Telefon: (49) 89 45 49 49 0 Fax: (49) 89 45 49 49 49 europe.sales@zetex.com	Telephone: (1) 631 360 2222 Fax: (1) 631 360 8222 usa.sales@zetex.com	Telephone: (852) 26100 611 Fax: (852) 24250 494 asia.sales@zetex.com	Telephone: (44) 161 622 4444 Fax: (44) 161 622 4446 hq@zetex.com

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